Supplementary Information

Observation of ferromagnetism in $CeCr_2Si_2C$ single crystals

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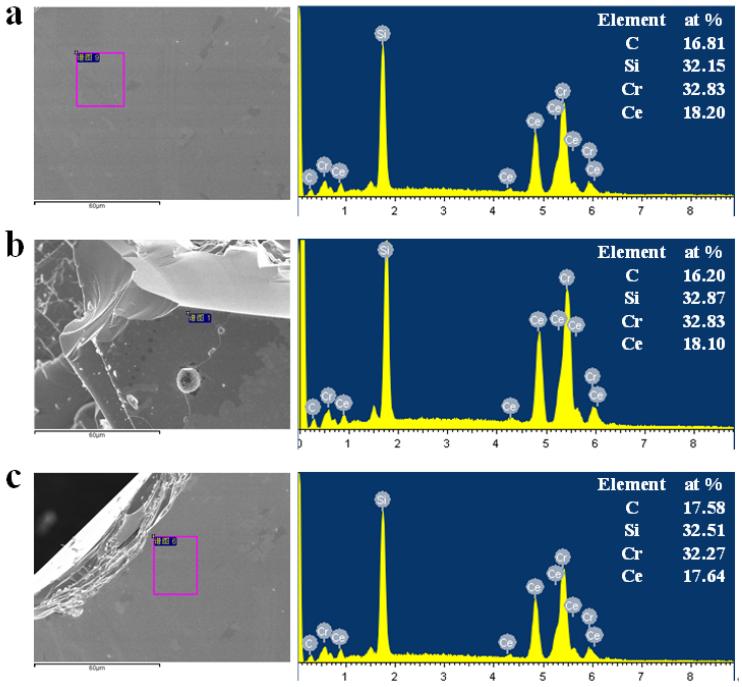

Fig. S1. EDXS spectra of $CeCr_2Si_2C$ bulk single crystals.

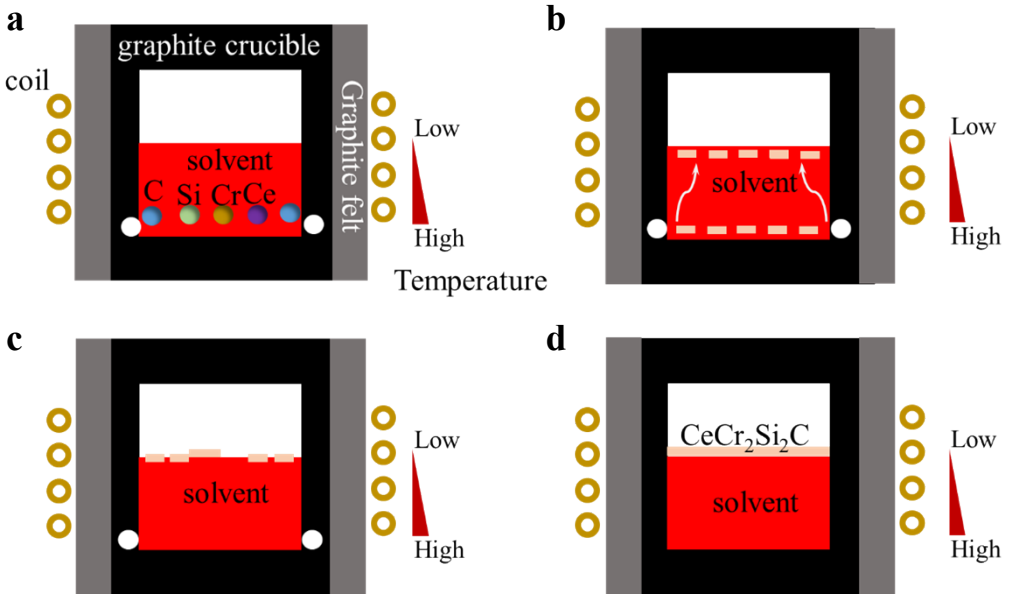

Fig. S2. Illustration of the growth mechanism for $CeCr_2Si_2C$ single crystals via high temperature solution technique.

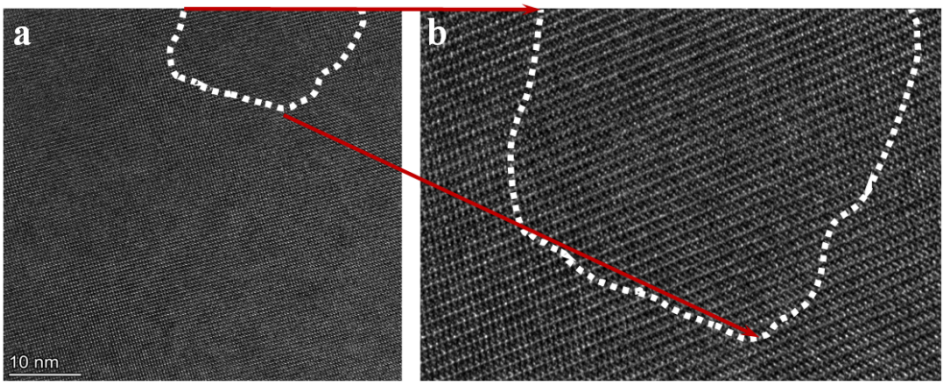

Fig. S3. (a) HRTEM and (b) magnified HRTEM images of $CeCr_2Si_2C$ single crystals, showing stacking disorders in the $CeCr_2Si_2C$ single crystals.

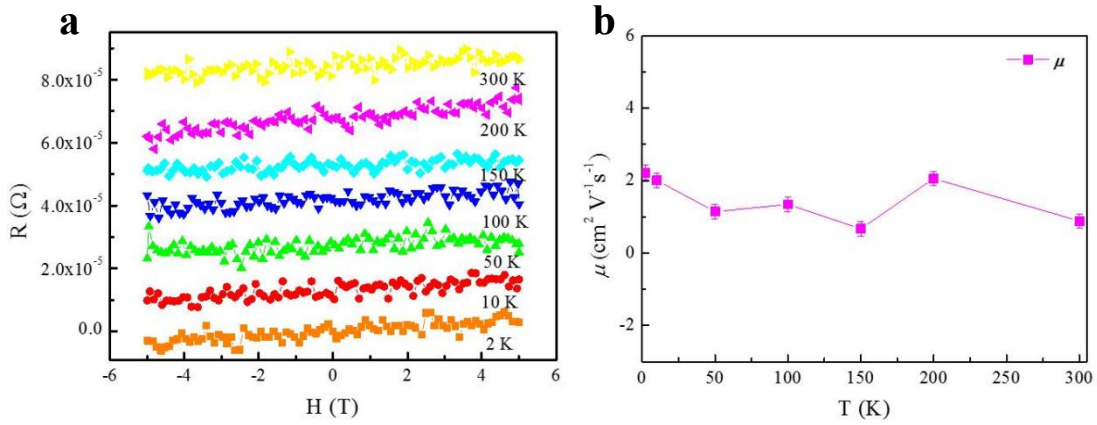

Fig. S4. (a) Hall resistivity (R - H) and (b) mobility (μ) measured in the temperature region of 2-300 K for $CeCr_2Si_2C$ bulk single crystals.

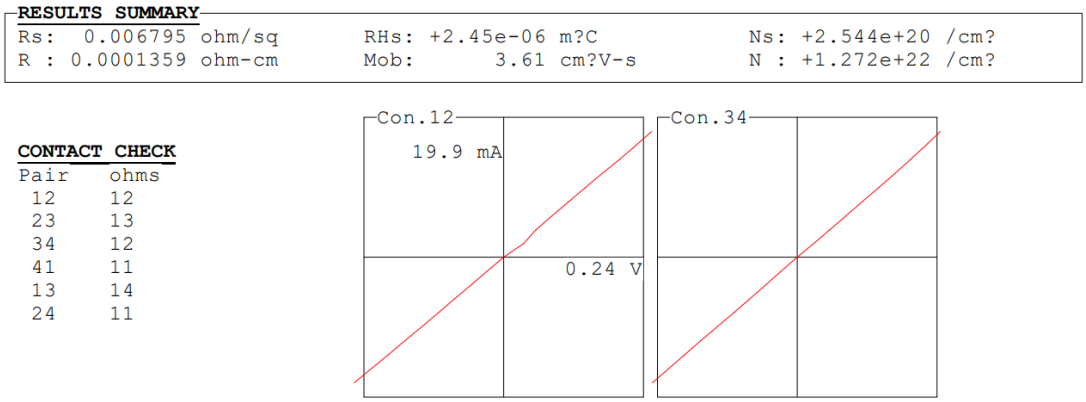

Fig. S5. Hall measurement results of $CeCr_2Si_2C$ single crystals.